L Number	Hits	Search Text .	DB	Time stamp
47	9	(257/737 or 257/786) and (aluminum or	USPAT	2004/05/26 19:43
		"Al") with (pad or electrode) and barrier		
		with ("Ni" or nickel) and (copper or "Cu") near (layers or films) and solder with		
		eutectic		
48	16	(257/737 or 257/786) and (aluminum or	USPAT	2004/05/26 19:17
		"Al") with (pad or electrode) and barrier		
;		with ("Ni" or nickel) and (copper or "Cu")		
49	g	and solder with eutectic (257/737 or 257/786) and (aluminum or	USPAT	2004/05/26 19:18
4.7		"Al") with (pad or electrode) and barrier		2004/03/20 13.10
		with ("Ni" or nickel) with (copper or		
		"Cu") and solder with eutectic		
50	3	(257/737 or 257/786) and (aluminum or	USPAT	2004/05/26 19:19
		"Al") with (pad or electrode) and (barrier or IBM) with ("Ni" or nickel) and (upper		
		near barrier or UBM) with (copper or "Cu")		
		and solder with eutectic		
51	7	(aluminum or "Al") with (wir\$3 or metal or	USPAT	2004/05/26 19:23
		cirsuit) and (copper or "Cu") with (pad or electrode) and (barrier or IBM) with ("Ni"		
		or nickel) and (upper near barrier or UBM)		
		with (copper or "Cu") and solder with		
	;	eutectic		
52	8	(aluminum or "Al") with (wir\$3 or metal or	USPAT	2004/05/26 19:23
		cirsuit) and (copper or "Cu") with (pad or electrode) and (barrier or LBM) with ("Ni"		!
		or nickel) and (under-bump near metallurgy		
		or UBM) with (copper or "Cu") and solder		
		with eutectic	110222	2004/05/06 00 50
53	3153	257/737	USPAT; US-PGPUB;	2004/05/26 20:53
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
54	226	257/737 and barrier with pad	USPAT;	2004/05/26 19:46
			US-PGPUB; EPO; JPO;	.
			DERWENT;	
			IBM_TDB	
55	2440	257/737 and pad	USPAT;	2004/05/26 19:46
			US-PGPUB; EPO; JPO;	
		-	DERWENT;	
			IBM_TDB	
56	1898	257/737 and pad and wir\$3	USPAT;	2004/05/26 20:38
Pater			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM_TDB	
57	0	(257/737 and pad and wir\$3) not (257/737	USPĀT;	2004/05/26 20:38
		and pad)	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
58	542	(257/737 and pad) not (257/737 and pad	USPAT;	2004/05/26 20:39
		and wir\$3)	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
59	1255	257/737 not (257/737 and pad and wir\$3)	USPAT;	2004/05/26 20:39
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
60	2623	257/738	USPAT;	2004/05/26 21:14
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
		<u> </u>	מתו ומםד	<u> </u>

1234 257/738 and pad with wir\$3 US-PGUB; EPO; JPO; DERWENT; IBM TDB US-PGPUB; E					
1234 257/738 and pad with wir\$3 DERWENT; ISM TDB USFAT; US-PCPUB; EPO; JPO; DERWENT; ISM TDB USFAT; US-P	61	2150	257/738 and pad	US-PGPUB;	2004/05/26 21:05
62					
STONGLESS STON	62	1224	257/730 and nad with wirks		2004/05/26 20:56
STOS428.pn. or DREWNT; IBM TOB USPAT; USPAT	02	1234	25///36 and pad with wirss		2004/03/20 20:36
63				EPO; JPO;	
14 \$705428.pn. or \$937320.pn. or \$937320.pn. or \$127731.pn. or \$127731.pn. or \$127731.pn. or \$127731.pn. or \$127731.pn. or \$1293457.pn. or \$1373137.pn. \$1373137.pn. \$1373137.pn. or \$140703.pn. or \$140703.pn. or \$140703.pn. or \$140703.pn. or \$140703.pn. or \$127731.pn. or \$1293457.pn. or \$127731.pn. or \$1293457.pn. or \$12573137.pn. or \$12573137.pn. or \$12573139.pn. or \$12573139.pn. or \$1257339.pn. or \$1257339.pn. or \$1257339.pn. or \$125739.pn. or \$1257		1		!	
S937320, pn. or 6127731, pn. or 6293457, pn. or 6293457, pn. or 6306751, pn. or 6140703, pn. or 6127731, pn. or 6127731, pn. or 6127731, pn. or 61293457, pn. or 6293457, pn. or 6293457, pn. or 6293457, pn. or 6293457, pn. or 6306751, pn. or 6306751, pn. or 6306751, pn. or 6306751, pn. or 6373137, pn. or 6306751, pn. or 6373137, pn. or 6293457, pn. or 6293457, pn. or 6306751, pn. or 6373137, pn. or 6306751, pn. or 6373137, pn. or 6306751, pn. or 6373137, pn. or 63747, prop. pn. pn. pn. pn. pn. pn. pn. pn. pn. p	63	14	5705428.pn. or	1 —	2004/05/26 21:01
6140703.m. or 6293457.pm. or 6306751.pm. or 6306751.pm. or 6373137.pm. or 6127731.pm. or 6127731.pm. or 6127731.pm. or 6127731.pm. or 6293457.pm. or 6293457.pm. or 6293457.pm. or 6293457.pm. or 6373137.pm. or 637413.pm. or 637413.		!	5937320.pn. or	US-PGPUB;	
64 7 7 5705428.pn. or 5937320.pn. or 6373137.pn. or 6140703.pn. or 6140703.pn. or 6140703.pn. or 6293457.pn. or 6306751.pn. or 6306751.pn. or 6373137.pn. or 63741371.pn. or			•	· · · · · · · · · · · · · · · · · · ·	
64 7 6373137.pn. or 6373137.pn. or 6127731.pn. or 6127731.pn. or 6127731.pn. or 6293457.pn. or 6293457.pn. or 6293457.pn. or 6373137.pn. or 63713137.pn. or 637131313.					
64 7 5705428.pn. or 5937320.pn. or 6127731.pn. or 6127731.pn. or 6293457.pn. or 6293457.pn. or 6306751.pn. or 6336751.pn. or 6336751.pn. or 6373137.pn. (257/738 and pad) not (257/738 and pad) USPAT; US-PGPUB; EPO; JPO; DERMENN; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERMENNT; IBM TDB USPAT; US-PGPUB; EPO; JPO;			-	_	
6127731.pn. or 6140703.pn. or 6293457.pn. or 6306751.pn. or 6306751.pn. or 6373137.pn. (257/738 and pad) not (257/738 and pad) with wir\$3) 66 281 257/739 257/739 257/786 67 2501 257/786 68 2000 257/786 and pad 257/786 and pad 257/786 and pad 70 17 (semiconductor or die or chip or IC) with (trench or recess or groove) with top near surface and (pad or electrode or contact) with slits 69 2004/05/26 22: 60 2004/05/26 22: 60 2004/05/26 22: 60 2004/05/26 22: 60 2004/05/26 22: 60 2004/05/26 22: 60 2004/05/26 22: 60 2004/05/26 22: 60 2004/05/26 22: 60 2004/05/26 22:	6.4	7	-	ייעק און וו	2004/05/26 21:01
6293457.pn. or 6306751.pn. or 6372137.pn. (257/738 and pad) not (257/738 and pad) USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IRM_TDB	04	, ,	-		2004/03/20 21:01
6306751.pn. or 6373137.pn. (257/738 and pad) not (257/738 and pad) With wir\$3) 66 281 257/739 USPAT; USPGUB; EPO; JPO; DERWENT; IBM TDB			-		
65 916 6373137.pn. (257/738 and pad) not (257/738 and pad with wir\$3) 66 281 257/739 USPAT; USPGUB; EPG; JPG; DERWENT; IEM TDB USPAT; USPGUB; EPG; JPG; DERWENT; IEM_TDB USPAT; USPGUB; EPG; JPG; DER		,			
With wir\$3 US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB			_		
EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; US	65	916	<u> </u>	•	2004/05/26 21:05
DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB			With Wir\$3)		
SPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB				DERWENT;	
US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	66	201	257/720	1	2004/05/26 22:15
DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	00	201	231/139		2004/03/20 22:13
IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB;		,			
67 2501 257/786 USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB					
EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; Surface and (pad or electrode or contact) US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	67	2501	257/786	_	2004/05/26 21:17
DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB					•
2000 257/786 and pad USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB					
US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB		0000	057/706	—	2004/05/26 22:06
EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	68	2000	257/786 and pad		2004/05/26 22:06
TBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB				EPO; JPO;	
501 257/786 not (257/786 and pad) 17 (semiconductor or die or chip or IC) with (trench or recess or groove) with top near surface and (pad or electrode or contact) with slits 2004/05/26 22: US-PGPUB; EPO; JPO; DERWENT; IBM_TDB 2004/05/26 22: US-PGPUB; EPO; JPO; DERWENT; IBM_TDB				1	
70 17 (semiconductor or die or chip or IC) with (trench or recess or groove) with top near surface and (pad or electrode or contact) with slits EPO; JPO; DERWENT; IBM_TDB EPO; JPO; DERWENT; IBM_TDB	69	501	257/786 not (257/786 and pad)	<u> </u>	2004/05/26 22:09
70 17 (semiconductor or die or chip or IC) with (trench or recess or groove) with top near surface and (pad or electrode or contact) with slits DERWENT; IBM_TDB 2004/05/26 22: DERWENT; IBM_TDB 2004/05/26 22: DERWENT; IBM_TDB					
70 (semiconductor or die or chip or IC) with USPAT; (trench or recess or groove) with top near surface and (pad or electrode or contact) DERWENT; IBM_TDB					
(trench or recess or groove) with top near US-PGPUB; surface and (pad or electrode or contact) EPO; JPO; with slits DERWENT; IBM_TDB				-	
surface and (pad or electrode or contact) EPO; JPO; with slits IBM_TDB	70	17		•	2004/05/26 22:14
IBM_TDB			_ ·		
			with slits		
71 196 (semiconductor or die or chip or IC) and USPAT; 2004/05/26 22:	71	196	(semiconductor or die or chip or IC) and	USPAT;	2004/05/26 22:20
(trench or recess or groove) with upper US-PGPUB;	_		(trench or recess or groove) with upper		
near surface and (pad or electrode or EPO; JPO; contact) with slits DERWENT;			1		
IBM_TDB			CONTRACT, WITTE STREET	Ť	
72 1919 257/750 USPAT; 2004/05/26 22: US-PGPUB;	72	1919	257/750	` \	2004/05/26 22:39
EPO; JPO;					
DERWENT;				DERWENT;	
73 IBM_TDB 231 (semiconductor or die or chip or IC) and USPAT; 2004/05/26 22:	73	231	(semiconductor or die or chip or TC) and	-	2004/05/26 22:31
(trench or recess or groove) with align\$4 US-PGPUB;	, 🤳		(trench or recess or groove) with align\$4	US-PGPUB;	
and (pad or electrode or contact) with EPO; JPO;			_		
slits DERWENT; IBM TDB			コエエクコ	}	
80 1645 (semiconductor or die or chip or IC) and USPAT 2004/05/26 22:	80	1645		_	2004/05/26 22:33
(trench or recess or groove) with align\$4 and (pad or electrode or contact) with	1				
(channels)			_		

81	1103	(semiconductor or die or chip or IC) and	USPAT	2004/05/26 22:34
		(trench or recess or groove) with align\$4		
		and (pad or contact) with (channels)		
82	2445	257/751	USPAT;	2004/05/26 22:39
	:		US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
83	393	257/751 and pad and barrier	USPAT;	2004/05/26 22:40
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	·
			IBM_TDB	
84	51	257/751 and pad and metallurgy	USPAT;	2004/05/26 22:41
			US-PGPUB;	·
			EPO; JPO;	
	1		DERWENT;	
			IBM_TDB	
85	124	(257/762 or 257/763 or 257/766) and pad	USPAT;	2004/05/26 22:44
		and metallurgy	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
86	212	(257/772 or 257/773 or 257/779) and pad	USPAT;	2004/05/26 22:49
		and metallurgy	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
87	218		USPAT;	2004/05/26 22:52
		and metallurgy	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		4077 4706 000 4074	IBM_TDB	0004/05/06 00 50
88	144	1	USPAT;	2004/05/26 22:52
		metallurgy	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		ę L	IBM TDB	